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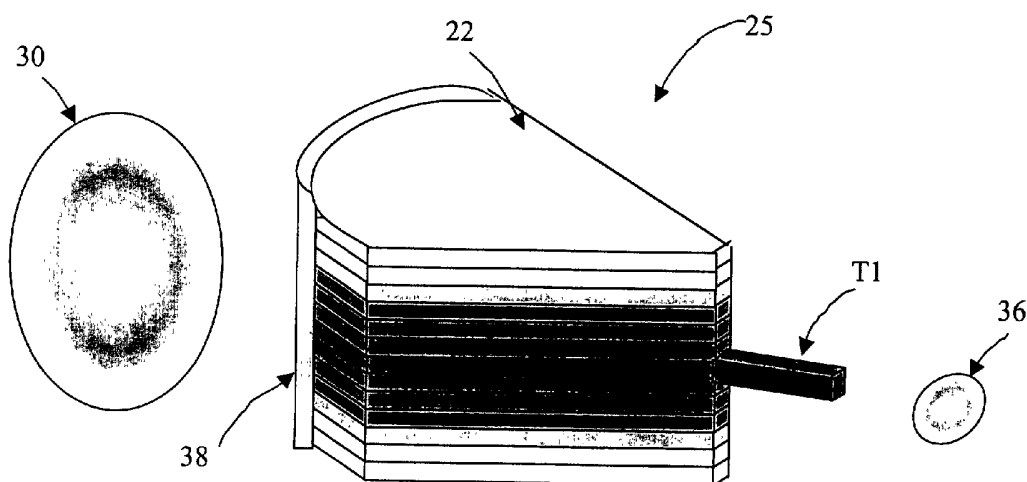
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(54) Title: **COMPACT THREE-DIMENSIONAL MODE SIZE CONVERTERS FOR FIBER-WAVEGUIDE COUPLING**



(57) **Abstract:** A 3D coupling system includes a layered structure that receives an input of a defined mode size. The layered structure includes a plurality of layers with varying indexes, and outputs a vertically mode converted beam associated with the input beam. A planar lens structure receives the vertically mode converted beam, and performs lateral mode conversion on the vertically mode converted beam. The 3D coupling structure outputs a laterally and vertically mode converted beam. A high index-contrast waveguide structure receives the laterally and vertically mode converted beam, and provides the laterally and vertically mode converted beam to a receiving device with less than 1dB loss.

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COMPACT THREE-DIMENSIONAL MODE SIZE CONVERTERS FOR FIBER-WAVEGUIDE COUPLING

PRIORITY INFORMATION

5 This application claims priority from provisional application Ser. No. 60/310,688 filed August 7, 2001, which is incorporated herein by reference in its entirety.

BACKGROUND OF THE INVENTION

10 The invention relates to the field of optics, and in particular to the formation of mode-size fiber-waveguide couplers.

 One of the characteristics of integrated optical devices is that they are based on single-mode high index-contrast waveguiding, which enables the dense integration of these devices on an optical chip. A major disadvantage of this approach is the
15 difficulty of coupling light to and from an optical fiber. By approximating the fiber mode by a gaussian distribution, the mode field diameter (MFD) of the fiber is defined as the diameter of the gaussian power distribution, and is approximately 15% larger than the core diameter.

 For a single-mode fiber (SMF) with a flat-end, the typical MFD is between 8
20 and 10 μm , and the mode cross-section is ideally circular. A lensed fiber has an output beam diameter of approximately 50% of the typical MFD and approximately a 20 μm focal length. A high index-contrast waveguide has a fundamental mode in the submicron range, depending on the aspect ratio of the rectangular waveguide core, the mode cross-section is strongly elliptical. This large mode-mismatch leads to a very
25 inefficient fiber-waveguide coupling where most of the power is lost to radiation. The coupling loss between fibers of different MFD, assuming that they are perfectly aligned, is defined as

$$\text{loss}(dB) = -10 \log \left\{ \frac{4}{\left(\frac{MFD_1}{MFD_2} + \frac{MFD_2}{MFD_1} \right)^2} \right\} \quad \text{Eq. 1}$$

 If the ellipticity of a waveguide is ignored and Eq. 1 is applied to get an
30 estimate, the loss associated with the coupling between a fiber and a waveguide with 5-

to-1 MFD ratio will be approximately 8.3 dB, which is less than 15% coupling efficiency. This is illustrated with a 2D numerical example hereinbelow. The numerical method used is the Finite Difference Time Domain (FDTD).

FIG. 1A is an electric field diagram and FIG. 1B is a graph of the transmission and reflection response illustrating coupling between a low index-contrast wide waveguide to a high index-contrast waveguide. FIG. 1A shows the low index-contrast wide waveguide having an index of approximately 1.05, a width of 4 μm , and a MFD of approximately of 4.8 μm , which is coupled to a high index-contrast narrow waveguide having an index of 3 and a width of 0.25 μm . The whole system is surrounded by air ($n=1$). FIG. 1B demonstrates that most of the power is lost to radiation and only 17% of the power is coupled into the waveguide mode.

Most approaches to solving this problem can be broadly classified into two types depending on whether the coupling schemes reside on the fiber side or the chip side. In the first type of coupling, a fiber tip is modified by tapering and/or lensing to bring the MFD of the fiber mode closer to that of the integrated waveguide. In the second type of coupling, the core of the integrated waveguide is adiabatically tapered so that the mode fields spreads out into the cladding to match the fiber mode size. Both types of coupling structures have lengths that are a few hundred microns.

Mode conversion schemes that work entirely on the fiber side can lead to critical alignment tolerances as the fiber mode size gets very small. Moreover, there is still a mis-match due to the different mode-shapes, because the fiber being circular and the waveguide being highly elliptical. For these reasons, it is preferable to concentrate most or all the mode matching efforts on the chip-side. Better alignment tolerances are obtained and the added advantage that one kind of fiber can be used to couple light into different photonic integrated circuits (PICs).

SUMMARY OF THE INVENTION

According to one aspect of the invention, there is provided a planar lens coupling system. The planar lens coupling system includes an input device providing an input beam of a defined mode size. A first interface layer of a defined index, the first layer includes the radial length of the planar lens. A high index-contrast waveguide is coupled to the first interface layer. The high index-contrast waveguide has the same index as the first interface layer and a mode size that is smaller than the

input beam. A second interface layer of a defined index is coupled to the first interface structure. The second interface layer is formed on the propagation axis as impedance matching at the location of maximum intensity. The first and second interface layers lower the mode size of the input beam laterally, thus providing improved coupling
5 between the input device and the high index-contrast waveguide.

According to another aspect of the invention, there is provided a 3D coupling system. The 3D coupling system includes a layered structure that receives an input of a defined mode size. The layered structure includes a plurality of layers with varying indexes, and outputs a vertically mode converted beam associated with the input beam.
10 A planar lens structure receives the vertically mode converted beam, and performs lateral mode conversion on the vertically mode converted beam. The planar lens structure outputs a laterally and vertically mode converted beam. A high index-contrast waveguide structure receives the laterally and vertically mode converted beam, and provides the laterally and vertically mode converted beam to a receiving device.

15 In still another aspect of the invention, there is provided a 3D coupling system that simultaneously performs vertical and lateral mode size conversion. In the vertical dimension of the 3D coupling system includes of a layered structure with quadratically varying refractive index that vertically converts the input fiber mode-size to match the vertical mode-size of the output high index contrast waveguide. In the lateral
20 dimension of the 3D coupling system includes as a planar lens structure. The planar lens structure includes a curved interface. The curved interface has a radius that is chosen to laterally convert the input fiber beam to match the lateral mode-size of the output high index contrast waveguide.

25 **BRIEF DESCRIPTION OF THE DRAWINGS**

FIGs. 1A and 1B are an electric field diagram and a graph of the transmission and reflection response obtained by FDTD simulations illustrating coupling between a low index-contrast wide waveguide to a high index-contrast waveguide;

FIGs. 2A and 2B are a schematic block diagram of a planar lens with a flat impedance-matching layer and a graph of the expected beam evolution when the input
30 is provided by a lensed fiber ($MFD=5\mu m$), respectively; FIGs. 2C-2D and 2E-2F are electric field amplitude diagrams and corresponding spectra graphs, respectively, obtained by FDTD simulation of an embodiment for coupling using a planar lens;

FIGs. 3A and 3B are a schematic block diagram of a planar lens with a conformal impedance-matching layer and a graph of the expected beam evolution when the input is provided by a lensed fiber (MFD=5 μ m), respectively; FIGs. 3C-3D and 3E-3F are electric field amplitude diagrams and corresponding spectra graphs, respectively, obtained by FDTD simulation of another embodiment for coupling using a planar lens;

FIGs. 4A and 4B are a schematic block diagram of a planar lens with a conformal impedance matching layer and a graph of the expected beam evolution when the input is provided by a flat-end fiber (MFD=10 μ m), respectively; FIGs. 4C and 4D are an electric field amplitude diagram and corresponding spectra graph for the two polarizations of the electric field (TE and TM), respectively;

FIGs. 5A-5B are schematic diagrams of two techniques of incorporating vertical and lateral mode conversion in accordance with the invention;

FIGs. 6A-6B and 6C-6D are schematic block diagrams (side view and top view) of the lensing structure of FIG. 5B and associated graphs of the expected beam evolution, respectively; and

FIGs. 7A-7B and 7C-7D are electric field diagrams and associated spectra graphs, respectively, obtained by FDTD simulations for propagation in the yz plane and xz plane of the coupler system shown in FIG. 5B; FIG. 7E is an estimated 3D transmission spectra for the two polarizations in the 3D coupling structure of FIG. 5B.

DETAILED DESCRIPTION OF THE INVENTION

The invention presents two basic ideas that allow efficient coupling within only a few μ m. For simplicity, it is assumed that the fiber mode is a gaussian beam that has a MFD of approximately 5 μ m if coming from a lensed SMF or 10 μ m if coming from a flat-end fiber. Alternatively, it can be considered that the input mode field is coming from a large low-index waveguide, which can be viewed as an intermediate stage between the fiber and the high index-contrast waveguide.

FIGs. 2A-2F illustrate an embodiment for coupling using planar lens. Since a mode of a fiber can be approximated by a gaussian beam, using gaussian optics to design lens-like structures can bring the MFD of the fiber down to that of the integrated waveguide mode. The analytical part of the design can then be based on the well-known transformation laws for gaussian beams using ABCD matrices. Numerical

validation and optimization is performed using the Finite Difference Time Domain (FDTD) method.

Coupling is achieved in this embodiment through lensing within a distance of only 6 μm . FIG. 2A shows the simple implementation of this idea. The planar lenslike structure 2 is designed to have specific properties, and the structure 2 is surrounded by air ($n_1=1$) or by another low-index material. Also, the structure 2 includes an interface layer 4. The interface layer 4 further includes a high index-contrast waveguide T1 that has an index n_3 that is 3. The width w_2 of the high index waveguide is 0.28 μm . The radial length r of the planar lens 2, in this embodiment, is 2.5 μm . The radial length r can also vary. The structure further includes an interface layer 6 that has an index $n_2 = \sqrt{n_1 n_3}$ that is 1.73 and a thickness $d = \lambda/4n_2$ that is 0.22 μm , and is formed on the propagation axis as impedance matching at the location of maximum intensity. The mode width w_1 is 5 μm , which is the MFD of the input fiber.

FIG. 2B depicts the expected beam evolution, which shows that the beam diameter can be reduced to well under 1 μm in less than 5 μm . The expected beam waist and phase front radius evolution along the device is obtained by ABCD formalism.

FIG. 2C demonstrates electric field amplitudes for the forward propagation (from fiber to chip) in the planar lens 2 obtained numerically. FIG. 2D depicts the spectra associated with the forward propagation, and shows that 82% of the input power from the fiber is transferred from the fiber to the waveguide and it is all coupled to the fundamental mode of the high index-contrast waveguide.

FIG. 2E demonstrates electric field amplitudes for the backward propagation (from chip to fiber) in the planar lens 2. FIG. 2F depicts the spectra associated with the backward propagation. The FDTD calculation of the associated spectrum shows that approximately 89% of the input power from the waveguide is transferred from the chip to the fiber and 82% of the waveguide power is coupled to the fundamental mode of the fiber.

The coupling between the two modes is equal in both directions whereas the total power is higher in the backward direction, because the radius of curvature r is very small, and the impedance matching interface layer 6 greatly deviates from the right thickness away from the center. Moreover, as plane wave fronts of the input

beam impinge on the strongly curved interface layer 6, additional reflections are caused due to phase mismatch.

FIGs. 3A-3F illustrate the coupler efficiency of a planar lens. The embodiment presents an improved version of the planar lens shown in FIG. 2A. In this embodiment
 5 the impedance matching layer is conformal to the interface between the high-index and the low-index material, thus the proper layer thickness for minimum reflection is approximately maintained along the interface. As discussed hereinbefore, a fiber can be approximated by a gaussian beam using gaussian optics to design lens-like structures that can bring the MFD of the fiber down to that of the integrated waveguide mode.
 10 The analytical part of the design can then be based on the well-known transformation laws for gaussian beams using ABCD matrices.

Also in this embodiment, coupling is achieved through lensing within a distance of only 6 μm . FIG. 3A shows that an interface layer 4 and an interface layer 6 are curved. The structure 2 is surrounded by air ($n_3=1$) or by another low-index material.
 15 The interface layer 4 further includes a high index-contrast waveguide T1 with an index n_1 of 3, and its radial length r_2 is 3 μm . The radial length r_2 can vary. The width w_2 of the high index waveguide T1 is 0.28 μm . The interface layer 6 has an index $n_2 = \sqrt{n_1 n_3}$ that is 1.73 and a thickness $d = \lambda/4n_2$ that is 0.22 μm , where λ is 1550 nm, is formed on the propagation axis as impedance matching at the location of
 20 maximum intensity. Also, the interface layer 6 has a radial length r_1 that is 3.3 μm . The radial length r_1 can also vary. The mode width w_1 of the input fiber is equal to the MFD of the fiber, which is 5 μm . The mode width w_1 can vary depending on the dimensions of the planar lens, 2.

FIG. 3B depicts the expected beam evolution, which shows that the beam
 25 diameter can be reduced to well under 1 μm and less than 5 μm . The expected beam waist and phase front radius evolution along the device is obtained by ABCD formalism.

FIG. 3C demonstrates electric field amplitudes for the forward propagation in the planar lens 2 of FIG. 3A. FIG. 3D depicts the spectra associated with the forward
 30 propagation. The FDTD calculation of the associated spectrum shows that approximately 89% of the input power is transferred from the fiber to the high index-contrast waveguide T1 all of which is coupled to the fundamental mode of the waveguide.

FIG. 3E demonstrates electric field amplitudes for the backward propagation in the planar lens 2. FIG. 3F depicts the spectra associated with the backward propagation. The FDTD calculation of the associated spectrum shows that approximately 98% of the input power from the waveguide is transferred from the chip to the fiber and 89% of the total waveguide power is coupled to the fundamental mode of the fiber.

The coupling between the two modes is equal in both directions whereas the total power is higher in the backward direction. This is due to the fact that as plane wave fronts of the input beam impinge on the strongly curved interface layer 6, additional reflections are caused due to phase mismatch.

The effect of the structure shown in FIG. 3A is the smoother transition from flat to curved wave fronts and vice versa. The thickness of the impedance matching interface layer 6 stays approximately the same on the propagation axis. The results shown in FIGs. 3C and 3F demonstrate an improved performance in both propagation directions and again verify the reciprocity of the coupling between individual modes. The design can be improved by making a gentler curve at the outer interface layer 6.

FIGs. 4A-4D demonstrate another embodiment of the planar lens designed for input or output provided by a flat-end fiber (MFD=10 μ m) in silicon dioxide (SiO₂) cladding. FIG. 4A shows that the interface layer 4 and the interface layer 6 are curved. The structure 2 is curved with silicon dioxide (SiO₂) cladding with an index n_3 that is 1.5. The input optical fiber, in this embodiment, is surrounded by air, and has an index n_5 that is 1. The interface layer 4 further includes a high index-contrast waveguide T1 with an index n_1 that is 3, and its radial length r_2 is 7 μ m. The radial length r_2 can vary. The width w_2 of the high index waveguide T1 is 0.28 μ m.

The interface layer 6 has an index $n_2 = \sqrt{n_1 n_3}$ that is 1.7 and a thickness $d = \lambda/4n_2$ that is 0.22 μ m is formed on the propagation axis as impedance matching at the location of maximum intensity, and has a radial length r_1 that is 7.5 μ m. The radial length r_1 is such that the impedance matching layer is conformal to the interface between the high-index and the low-index material, thus the proper layer thickness is approximately maintained along the interface.

FIG. 4B depicts the expected beam evolution, which shows that the beam diameter can be reduced to less than 1 μ m in less than 11 μ m. The expected beam waist and phase front radius evolution along the device is obtained by ABCD

formalism.

FIG. 4C also shows electric field amplitudes for the forward propagation in the planar lens 2 of FIG. 4A. FIG. 4D depicts the spectra associated with the forward propagation. The FDTD calculation of the associated spectrum shows that
5 approximately between 94% and 91% of the input is transferred from the fiber to the TE polarized and the TM polarized mode of the waveguide, respectively.

FIGs. 5A-5B show two techniques of incorporating vertical and lateral mode conversion. The previous discussions, herein, regarding the planar lens are in two dimensions and addressed the problem of lateral mode-size conversion, while ignoring
10 variations in the vertical dimension. The treatment of the vertical direction is not obvious in the case of lensing. In theory, the same scheme can work in 3D using a spherical or ellipsoidal lens, the theoretical analysis can be performed separately for the two q-parameters of elliptical gaussian. However, the fabrication of a structure with one or more interfaces with 3D curvature can be a very difficult task. A different
15 approach for vertical focusing must be used, which is suited for fabrication in the vertical direction. The gaussian beam propagation in a quadratic index media is an obvious choice for vertical lensing, and can be a layered structure with the index varying quadratically from layer to layer.

In particular, FIG. 5A demonstrates a 3D coupler system 18. The 3D coupler
20 system 18 includes a layered structure 22 and a lateral mode conversion planar lens 26, and performs both lateral and vertical mode conversion of an input electromagnetic signal 20 of a defined mode size. The layered structure 22 receives the electromagnetic signal 20 and performs vertical mode conversion by way of its various graded index layers 21, and outputs an electromagnetic signal 24. The lateral mode
25 conversion planar lens 26 receives the electromagnetic signal 24, and performs lateral mode conversion on the signal 24 and outputs an electromagnetic 28. The electromagnetic signal 28 has incorporated both lateral and vertical mode conversions, which can be provided to a 3D high index-contrast waveguide or other coupling mechanisms.

30 FIG. 5B show a 3D coupler 32 that combines the vertical and lateral lensing mechanisms of 22 and 26, respectively, of FIG 5A. The 3D coupler 25 performs vertical and lateral mode conversion on an electromagnetic signal 30 without requiring two separate vertical and lateral mode conversion modules, and outputs an

electromagnetic signal 36 through a high index-contrast waveguide 34 without incorporating substantial reflections and beam spreading in the orthogonal directions. The layer 38 provides impedance matching with proper thickness and index to minimize reflections.

FIGs. 6A-6D illustrate the coupling efficiency of the system described in FIG. 5B. To illustrate the operation of such a coupler in a numerical example, the entire 3D structure is to be modeled over a volume of approximately $10^3 \mu\text{m}^3$, which is prohibitive for a full 3D FDTD simulation. The analysis is directed to the xz-plane and yz-plane, and utilizes the fact the evolution of elliptical Gaussian beam can be traced separately in two dimensions. The propagation of the gaussian beam in the layered medium 22 is treated first, the associated effective index is used to link the analyses.

FIG. 6A shows the layered structure 22, which has an index variation of the form

$$n(x, y) = \begin{cases} n_i \left(1 - \frac{x^2}{2h^2} \right) & |x| \leq a \\ n_0 & |x| > a \end{cases} \quad \text{Eq. 2}$$

where, for continuity of the index distribution, $h = a / \sqrt{2(1 - n_0/n_i)}$. The length of the layered structure along the z direction is $\pi h/2$, which is half the period of variation of the Gaussian beam width in the graded region 21 to ensure maximum beam width narrowing in the x direction. Analytically, the expected variation of the beam width along the z direction is computed and from the variation of the associated effective index is given by:

$$n_e(z) = n_i \left[1 - \frac{1}{(k_0 n_i w(z))^2} \right] \quad \text{Eq. 3}$$

In this embodiment, the value of n_i is 2.2 and n_0 is 1.5 and a is $6 \mu\text{m}$. These particular index values are chosen such that the graded index is in the range approximately achievable with silicon nitrides. The waveguide T1 also has an index of 2.2 and cladding of 1.5. With h being $7.52 \mu\text{m}$, the focal length is $f_1 = \pi h/2 \approx 11.8 \mu\text{m}$. In theory the quadratic index variation of the index given by Eq. 2 is continuous. In practice the variation of the index is piecewise consisting of a multitude of layers with finite thickness. In this embodiment the thickness of each layer is 200nm . The impedance matching layer 38 has an index that is 1.45 and thickness $0.26 \mu\text{m}$.

FIG. 6B depicts the expected beam evolution that shows that the beam diameter can be reduced to less than $1\ \mu\text{m}$ in less than $12\ \mu\text{m}$. The expected beam waist and phase front radius evolution along the device is obtained by ABCD formalism.

FIG. 6C shows the planar lens 32 that includes an interface layer 40 and an
 5 interface layer 42 that are curved. The structure 32 is surrounded by air ($n_3=1$). The interface layer 40 further includes a high index-contrast waveguide T1 with an index of 2.2, and its radial length r_2 is $5.25\ \mu\text{m}$. The radial length r_2 can vary. The width w_2 of the high index waveguide T1 is $0.28\ \mu\text{m}$. The interface layer 42 has an index $n_2 = \sqrt{n_1 n_3}$ that is 1.45 and a thickness d that is $\lambda/4n_2 = 0.26\ \mu\text{m}$, where λ is $1550\ \text{nm}$,
 10 which is formed on the propagation axis as impedance matching at the location of maximum intensity. Also, the interface layer 42 has a radial length r_1 that is $5.75\ \mu\text{m}$. The radial length r_1 can also vary. The mode width w_1 is equal to the MFD of the input fiber, which is $10\ \mu\text{m}$. Also, the particular radii r_1 and r_2 are chosen so that a focal length f_2 of the planar lens 32 is equal to the focal f_1 of the layered structure 22,
 15 which is $11.8\ \mu\text{m}$.

FIG. 6D depicts the expected beam evolution of the planar lens 32, which shows that the beam diameter can be reduced to well under $1\ \mu\text{m}$ and less than $12\ \mu\text{m}$. The expected beam waist and phase front radius evolution along the device is obtained by ABCD formalism.

20 FIGS. 7A-7D show the electric field and associated spectra obtained by FDTD for forward propagation in the yz plane and xz plane of the coupler system shown in FIG. 5B.

FIG. 7A demonstrates electric field amplitudes for the forward propagation (from fiber to chip) in the layered structure 32 of FIG. 6A. FIG. 7B depicts the
 25 spectra associated with the forward propagation. The FDTD calculation of the associated spectrum shows that approximately between 93% and 93.5% of the input is transferred from the fiber to the TE and TM mode of the waveguide, respectively. The same results are obtained for coupling from the waveguide to the fiber.

FIG. 7C demonstrates electric field amplitudes for the forward propagation in
 30 the planar lens 32 of FIG. 6C. FIG. 7D depicts the spectra associated with the forward propagation. The FDTD calculation of the associated spectrum shows that approximately between 91 and 93.3% of the input is transferred from the fiber to the TE and TM mode of the waveguide, respectively. Same results are obtained for

coupling from the waveguide to the fiber.

An estimate of the 3D coupling efficiency can be obtained as a product of the spectra for the mode-to-mode 2D coupling of xz and yz planes as shown in FIG. 7E. At 1550nm the coupling efficiency is $0.93.5 \times 0.91 = 0.85$ for the TE polarization and
5 $0.93 \times 0.93.3 = 0.87$ for the TM polarization, which corresponds to a coupling loss of well under 1 dB. However, this value is much more efficient than any other technique in the art. Better coupling can be obtained with an optimized design of the layered structure 32 where radiation loss seems more likely to occur.

The invention provides an overall 0.5-1 dB loss for the high index-contrast
10 lenses. These structures are very compact and are sized at approximately $10 \mu\text{m}$. Implementing the invention can be possible using existing material systems and fabrication. Efficiency of the invention can be improved by reducing the radiation and by using more elaborate lens and AR design.

Although the present invention has been shown and described with respect to
15 several preferred embodiments thereof, various changes, omissions and additions to the form and detail thereof, may be made therein, without departing from the spirit and scope of the invention.

What is claimed is:

CLAIMS

1. A planar lens coupling system comprising:
 - an input device fiber providing an input beam of a defined mode size;
 - a first interface layer of a defined index, said first layer including the radial
 - 5 length of said planar lens;
 - a high index-contrast waveguide coupled to said first interface layer, said high index-contrast waveguide having the same index as the first interface layer and a mode size that is smaller than said input beam; and
 - a second interface layer of a defined index coupled to said first interface
 - 10 structure, said second interface layer formed on the propagation axis as impedance matching at the location of maximum intensity, wherein
 - said first and second interface layers lower the mode size of said input beam, thus providing coupling between said input device and said high index-contrast waveguide.
 - 15
2. The planar lens of claim 1, wherein said high index-contrast waveguide comprises an index of 3.
3. The planar lens of claim 2, wherein said radial length is $2.5\ \mu\text{m}$.
4. The planar lens of claim 3, wherein said first interface layer comprises an index of
- 20 3.
5. The planar lens of claim 3, wherein said second interface layer comprises an index of 1.73.
6. The planar lens of claim 5, wherein the high index-contrast waveguide comprises a width of $0.28\ \mu\text{m}$.
- 25 7. The planar lens of claim 6, wherein said second interface layer has a thickness of $0.22\ \mu\text{m}$.
8. The planar lens of claim 7 further comprising a forward and backward propagation.
9. The planar lens of claim 8, wherein said forward propagation is arranged so that said high index-contrast waveguide is coupled to a chip element.

10. The planar lens of claim 8, wherein said backward propagation is arranged so that said high index-contrast waveguide is coupled to said input fiber.
11. The planar lens of claim 9, wherein said forward propagation shows an efficiency of 82%.
- 5 12. The planar lens of claim 10, wherein said backward propagation shows an efficiency of 82%.
13. The planar lens of claim 1 further comprising a silicon dioxide cladding covering said planar lens structure.
14. The planar lens of claim 10, wherein said second interface layers has radial length
10 of approximately 3 μm .
15. The planar lens of claim 9, wherein said forward propagation shows an efficiency of 89%.
16. The planar lens of claim 10, wherein said backward propagation shows an efficiency of 89%.
- 15 17. A 3D coupling system comprising:
a layered structure that receives an input of a defined mode size, said layered structure includes a plurality of layers with varying indexes, and outputs a vertically mode converted beam associated with said input beam;
a planar lens structure that receives said vertically mode converted beam and
20 performs lateral mode conversion on said vertically mode converted beam, said planar lens structure outputs a laterally and vertically mode converted beam; and
a high index-contrast waveguide structure receiving said laterally and vertically mode converted beam and providing said laterally and vertically mode converted beam to a receiving device.
- 25 18. The 3D coupling system of claim 17, wherein said indexes of said layers vary quadratically.
19. The 3D coupling system of claim 17, wherein said high index-contrast waveguide comprises an index of 2.2

20. The 3D coupling system of claim 19, wherein said high index-contrast waveguide comprises a cladding with an index of 1.5.
21. The 3D coupling system of claim 17, wherein said planar lens further comprises a first interface layer of a defined index, said first layer including the radial length of
5 said planar lens.
22. The 3D coupling system of claim 21, wherein said planar lens further comprises a second interface layer of a defined index that is coupled to said first interface structure, said second interface layer is formed on the propagation axis as impedance matching at the location of maximum intensity.
- 10 23. The 3D coupling system of claim 22, wherein said first and second interface layers lowering the mode size of said input beam, thus providing coupling between said input fiber and said high index-contrast waveguide.
24. The planar lens of claim 23, wherein said radial length is $5.25\ \mu\text{m}$.
25. The planar lens of claim 24, wherein said first interface layer comprises an index
15 of 2.2.
26. The planar lens of claim 24, wherein said second interface layer comprises an index of 1.5.
27. The planar lens of claim 26, wherein the high index-contrast waveguide comprises a width of $0.28\ \mu\text{m}$.
- 20 28. The planar lens of claim 27, wherein said second interface layer has a thickness of $0.26\ \mu\text{m}$.
29. The planar lens of claim 28 further comprising a forward and backward propagation.
30. The planar lens of claim 28, wherein said forward propagation is arranged so that
25 said high index-contrast waveguide is coupled to a chip element.
31. The planar lens of claim 28, wherein said backward propagation is arranged so that said high index-contrast waveguide is coupled to said input fiber.

32. The planar lens of claim 29, wherein said forward and backward propagation shows an efficiency of approximately 93 % for the layered structure.

33. The planar lens of claim 29, wherein said forward propagation shows an efficiency of approximately 93 % for the planar lens.

5 34. A 3D coupling system that simultaneously performs vertical and lateral mode conversion, said 3D coupling system comprising:

a layered structure in the vertical dimension of said 3D coupling system with quadratically varying refractive index that converts an input fiber mode-size to match the vertical mode-size of an output high index contrast waveguide, and

10 a planar lens structure in the lateral dimension of said 3D coupling system having a curved interface, said curved interface having a radius that is chosen to laterally convert the input fiber mode-size to match the lateral mode-size of the output high index contrast waveguide.

15 35. The 3D coupling system of claim 34 further comprising an impedance matching layer of proper index and a quarter-wavelength thickness to minimize reflections.

36. The 3D coupling system of claim 34, wherein said vertical and lateral mode conversion have the same focal lengths.

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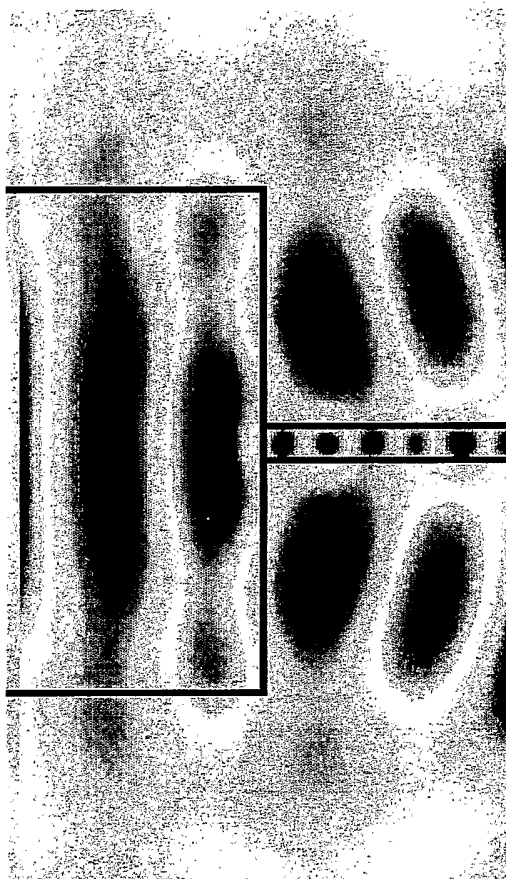
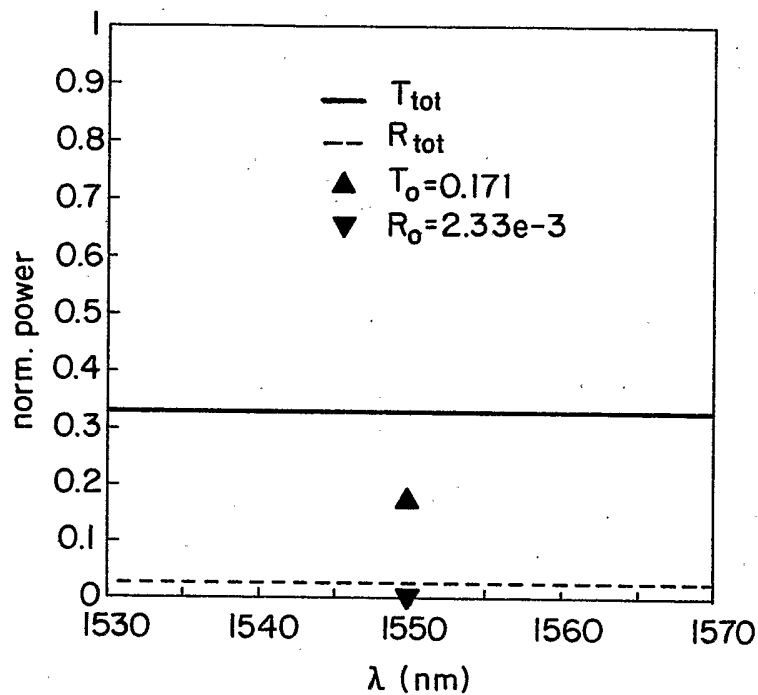
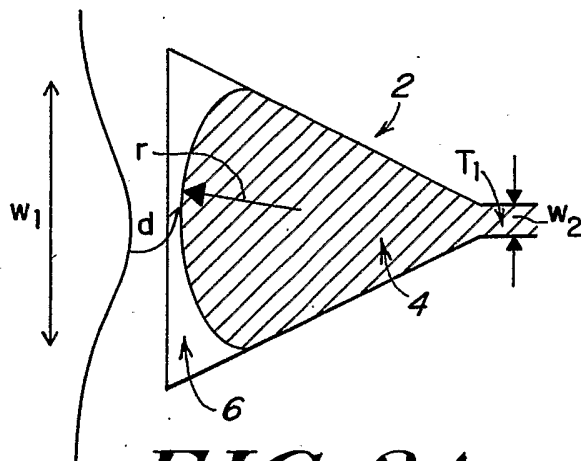
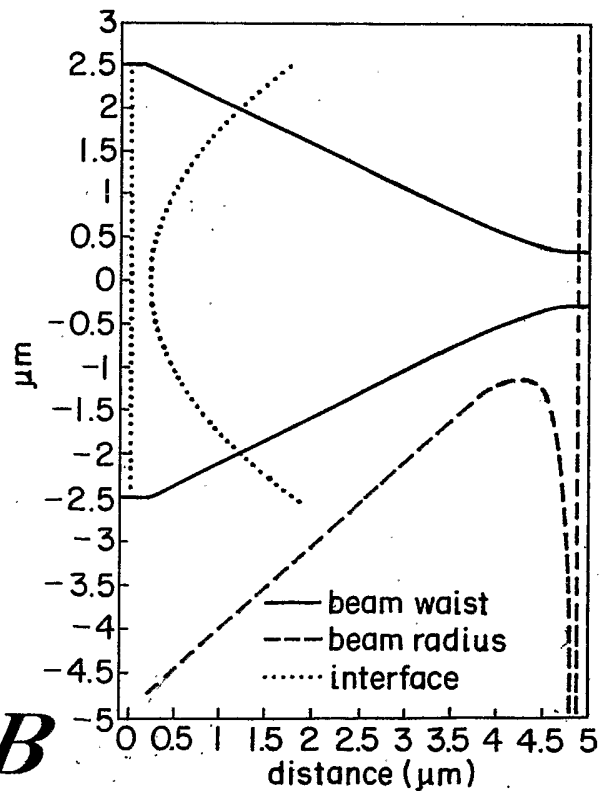
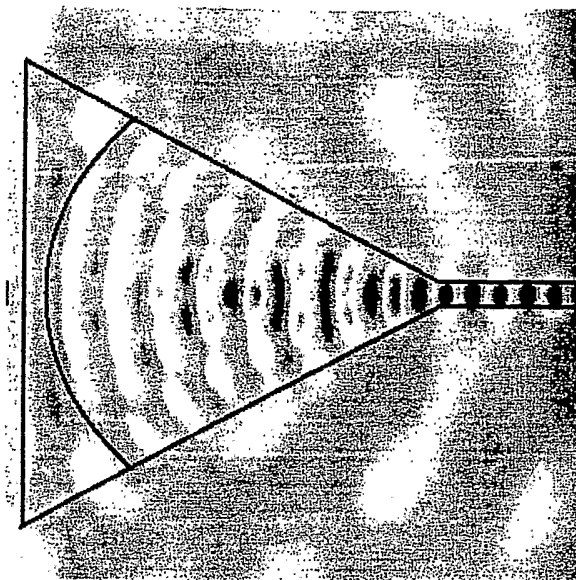
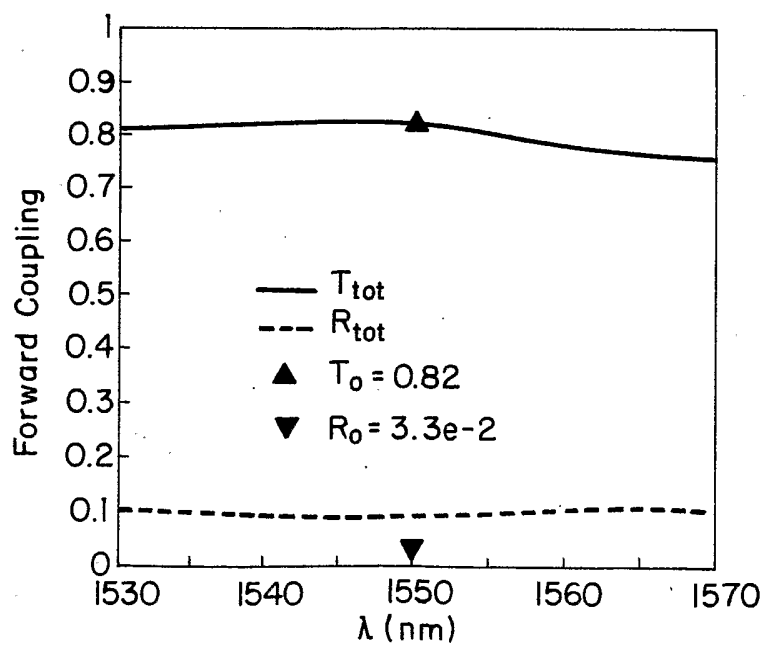


FIG. 1A

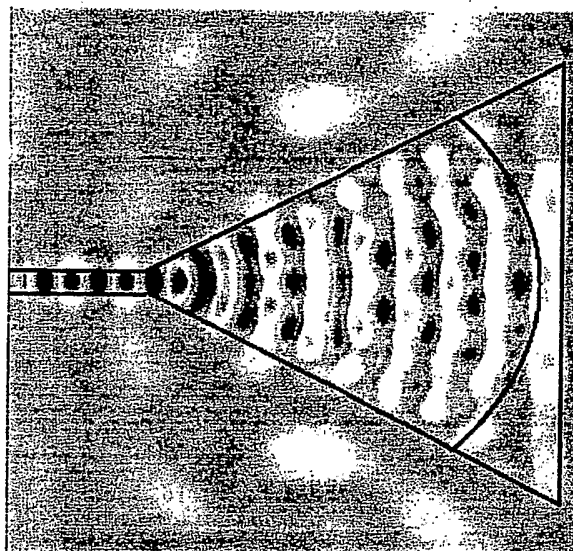
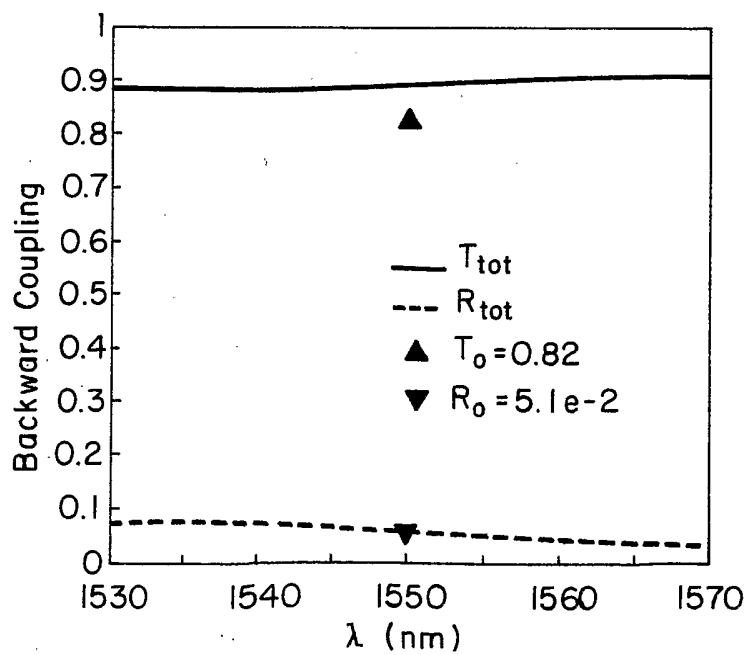
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**FIG. 1B****FIG. 2A****FIG. 2B**

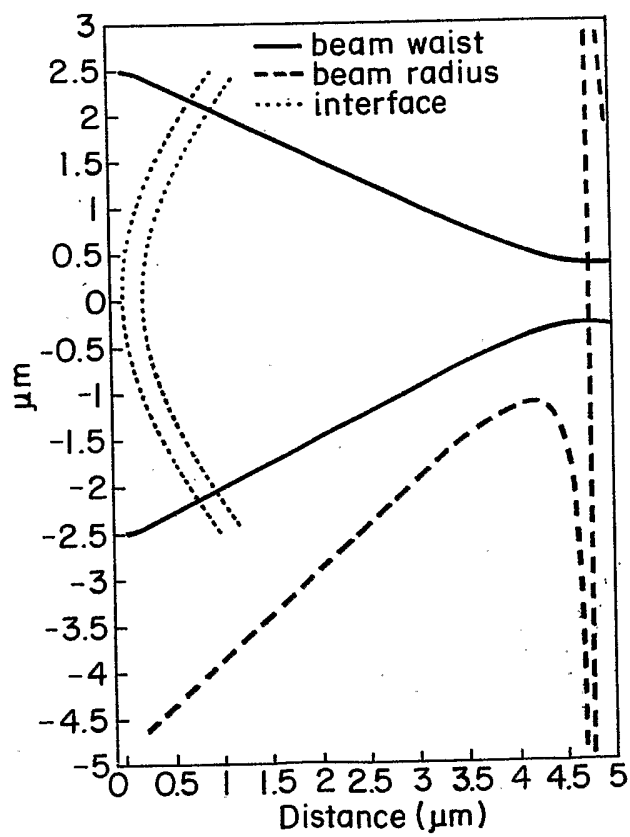
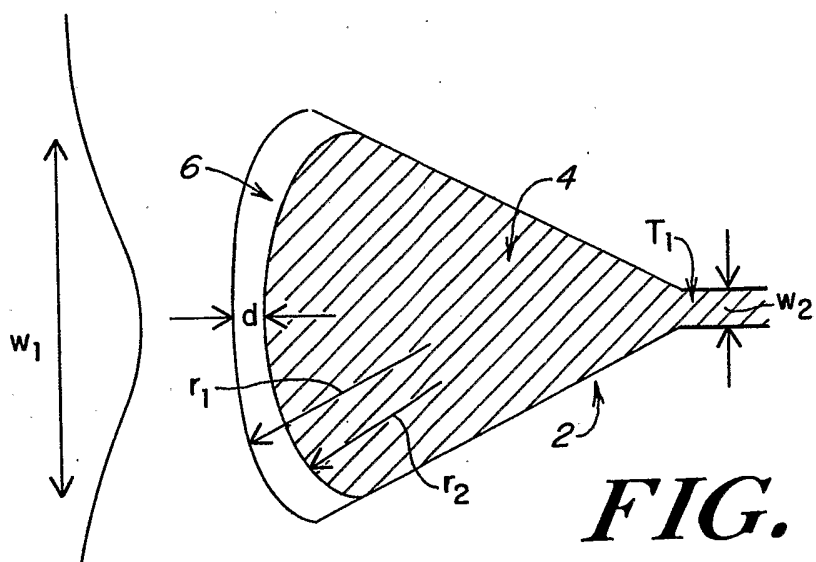
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*FIG. 2C**FIG. 2D*

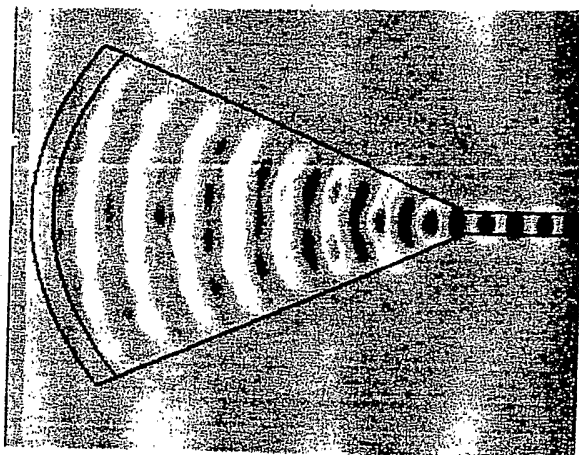
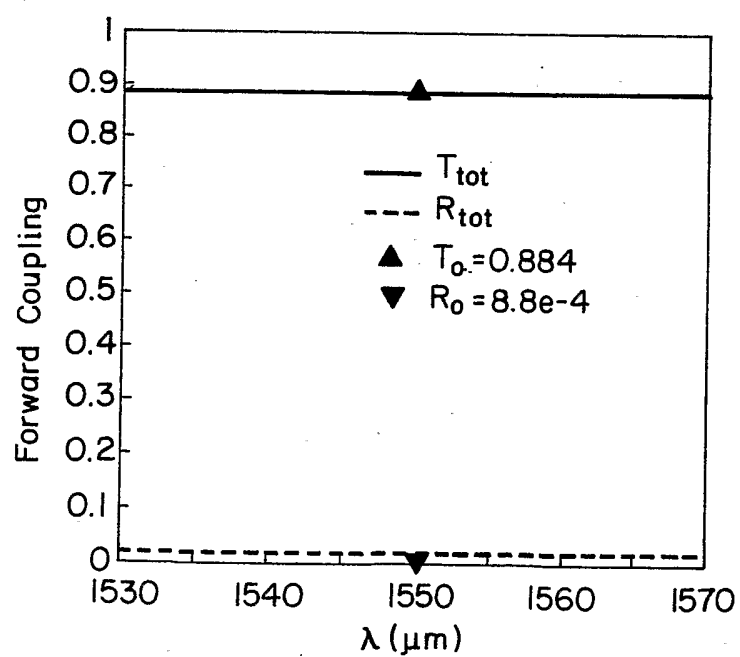
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*FIG. 2E**FIG. 2F*

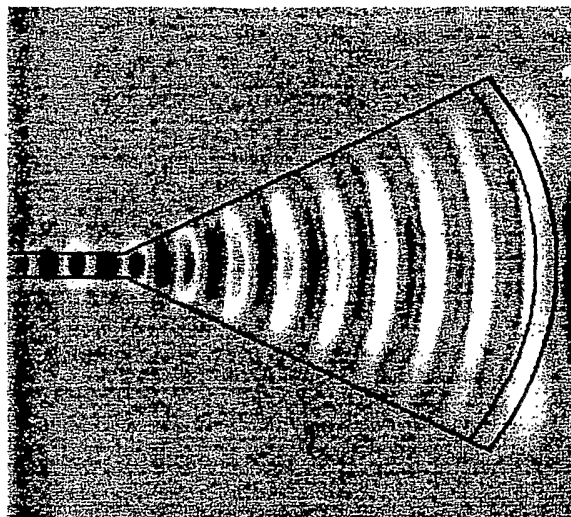
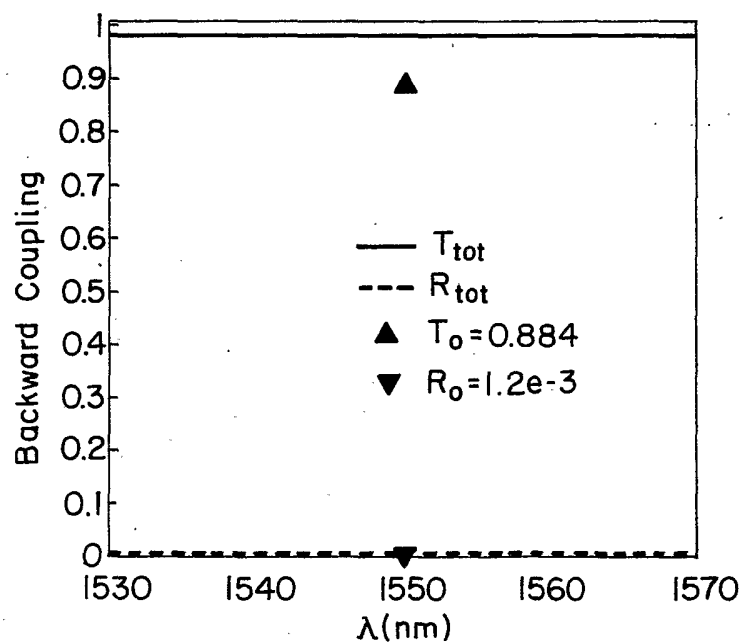
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**FIG. 3B**

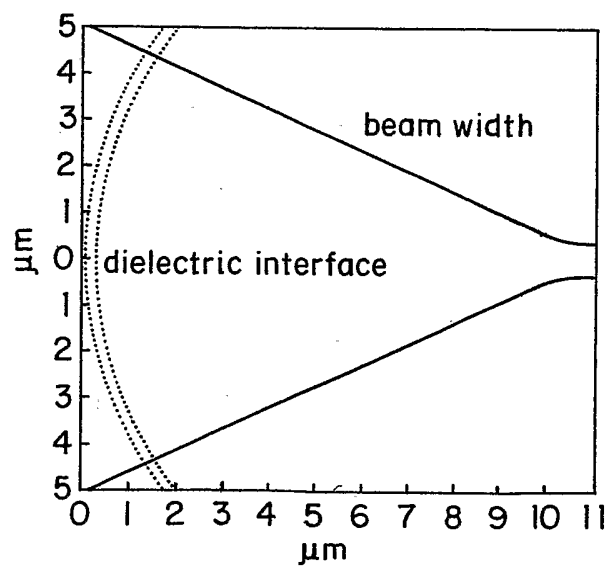
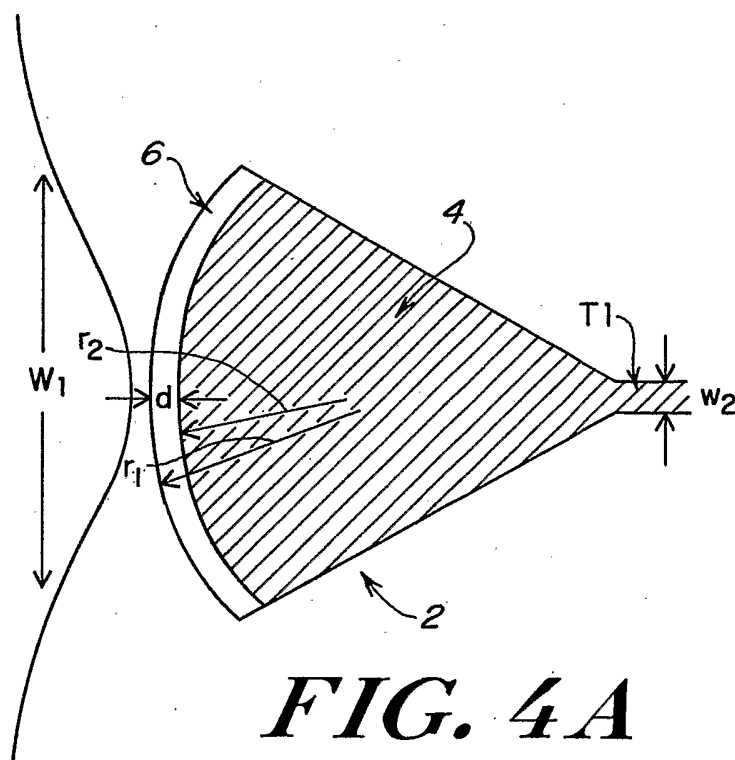
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*FIG. 3C**FIG. 3D*

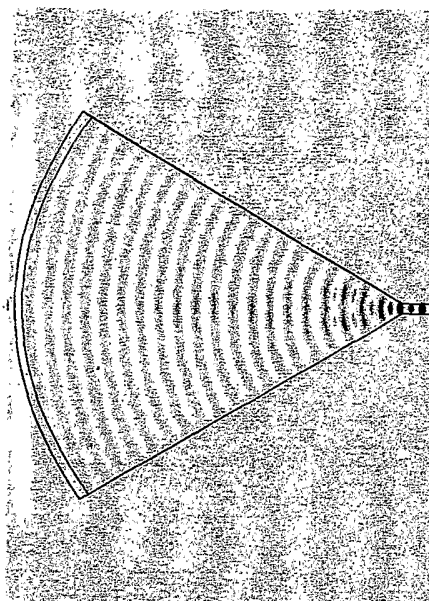
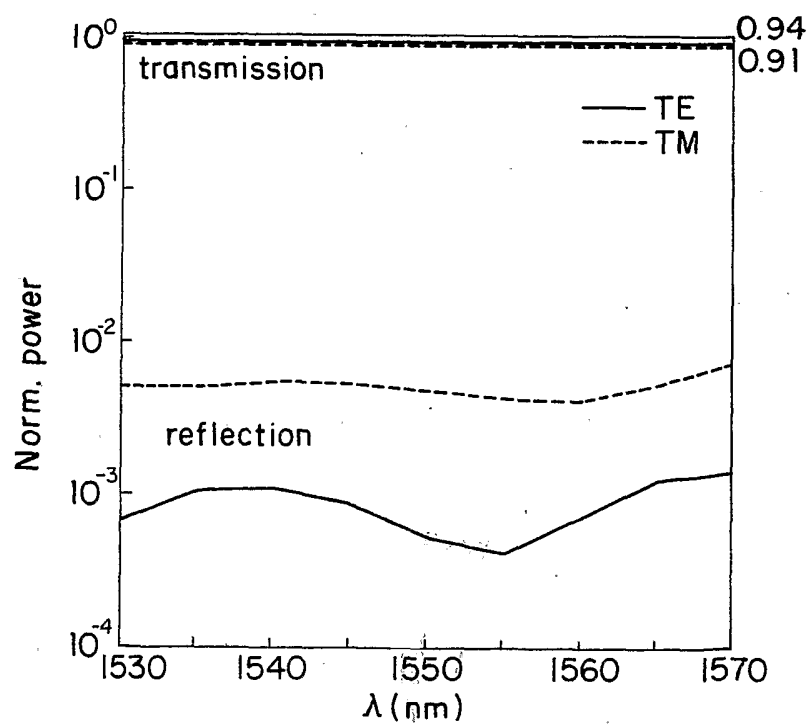
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*FIG. 3E**FIG. 3F*

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**FIG. 4C****FIG. 4D**

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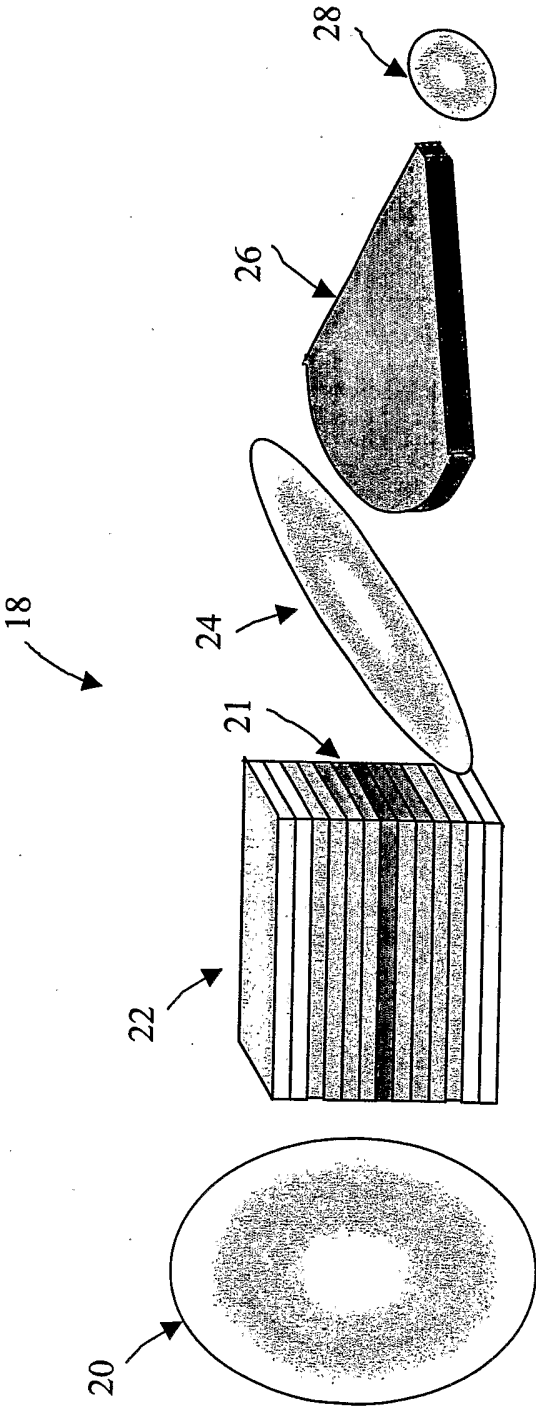


FIG. 5A

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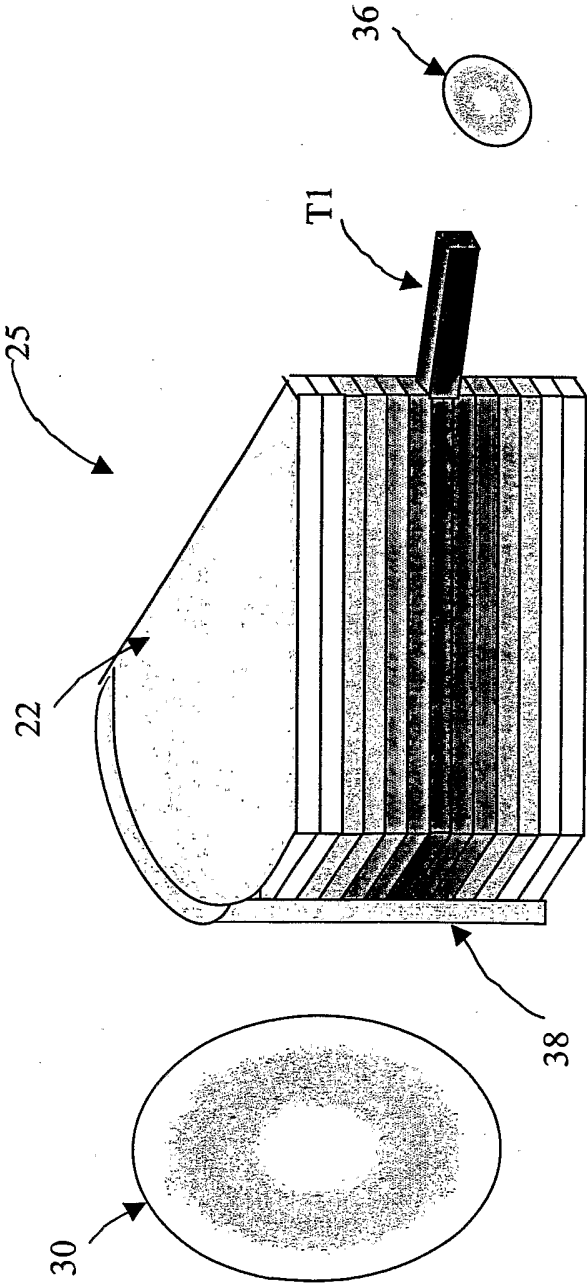


FIG. 5B

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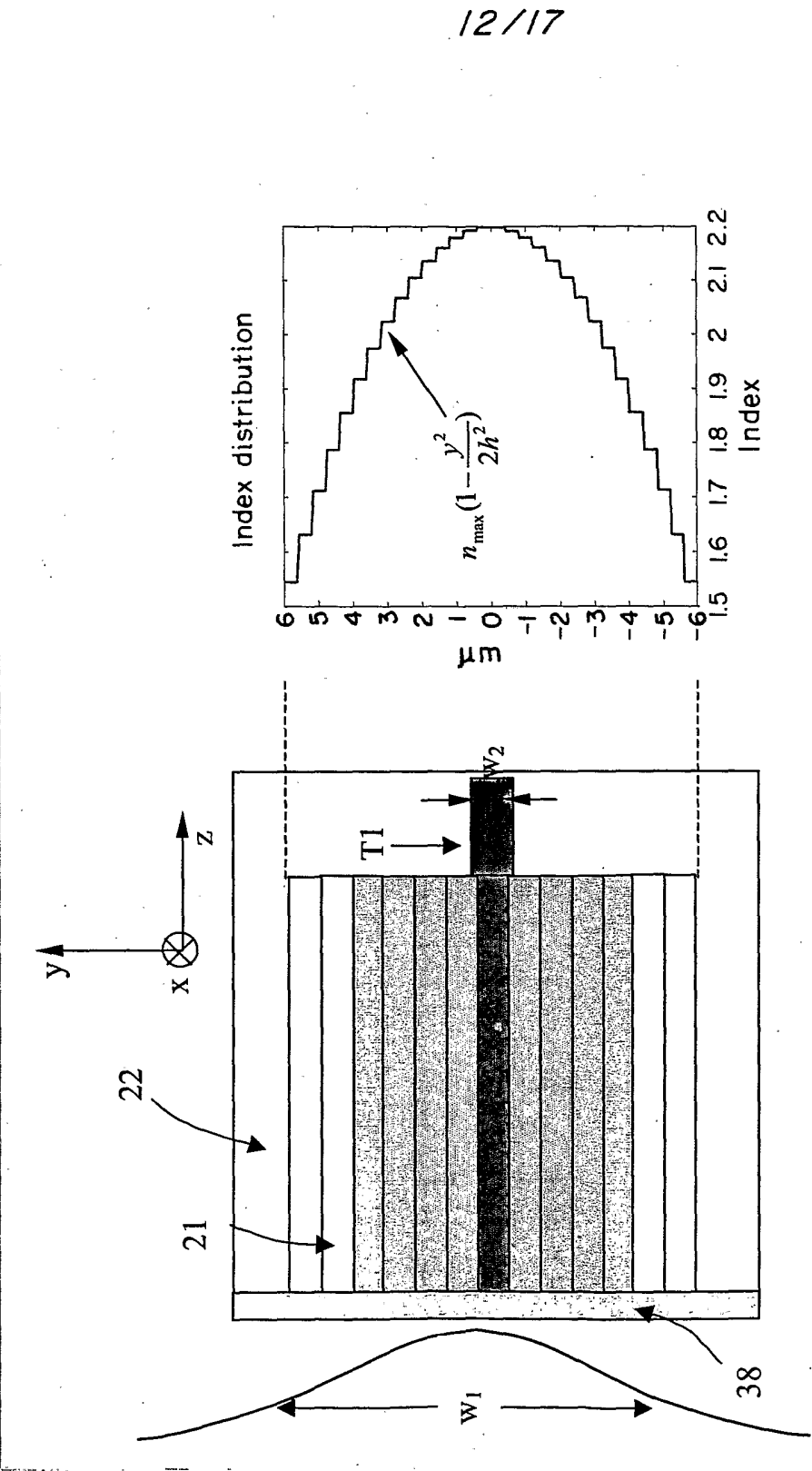
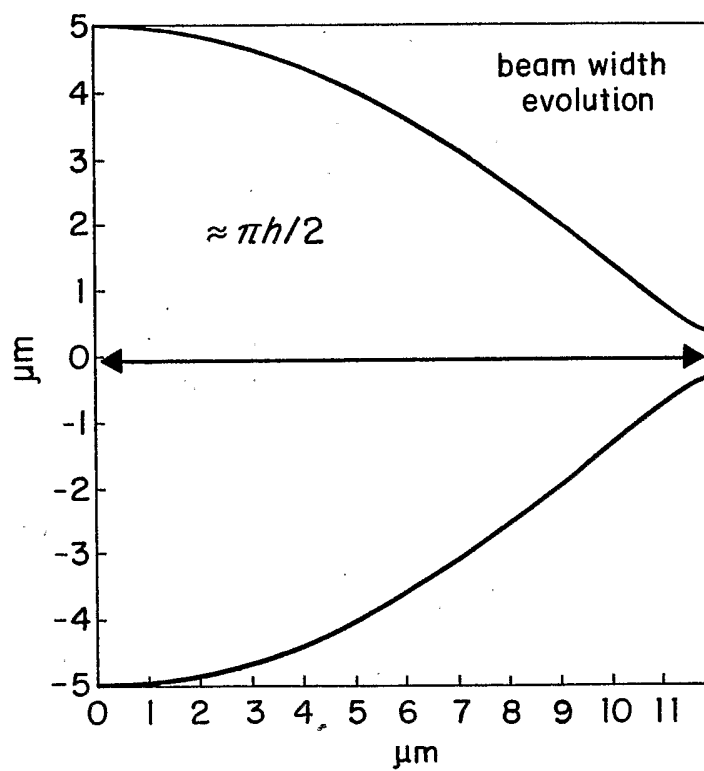
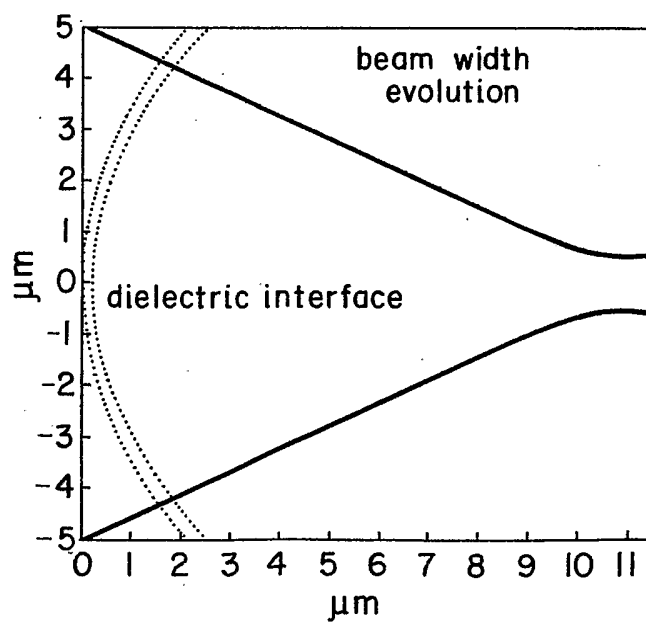
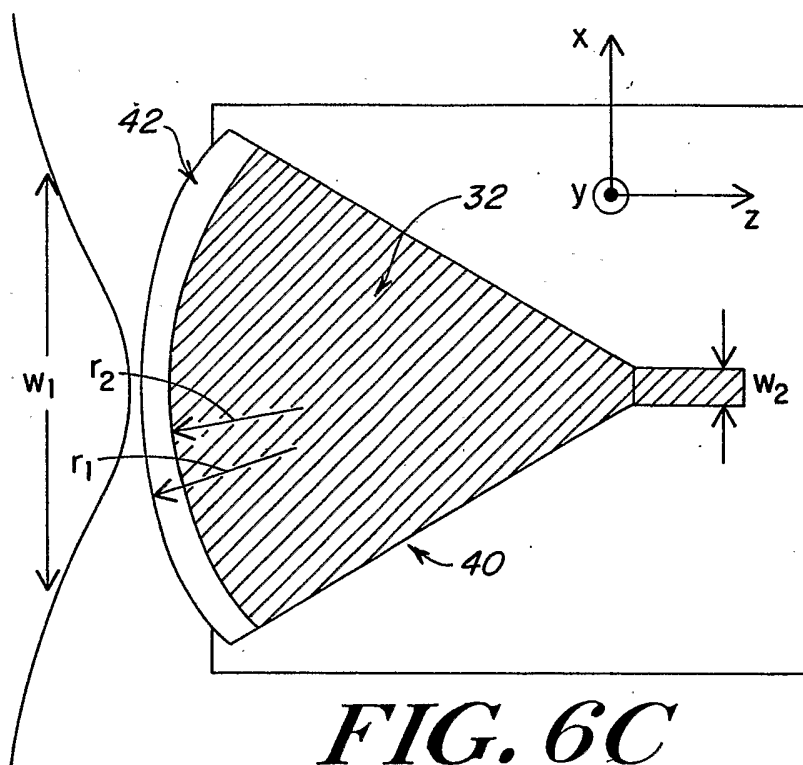


FIG. 6A

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**FIG. 6B**

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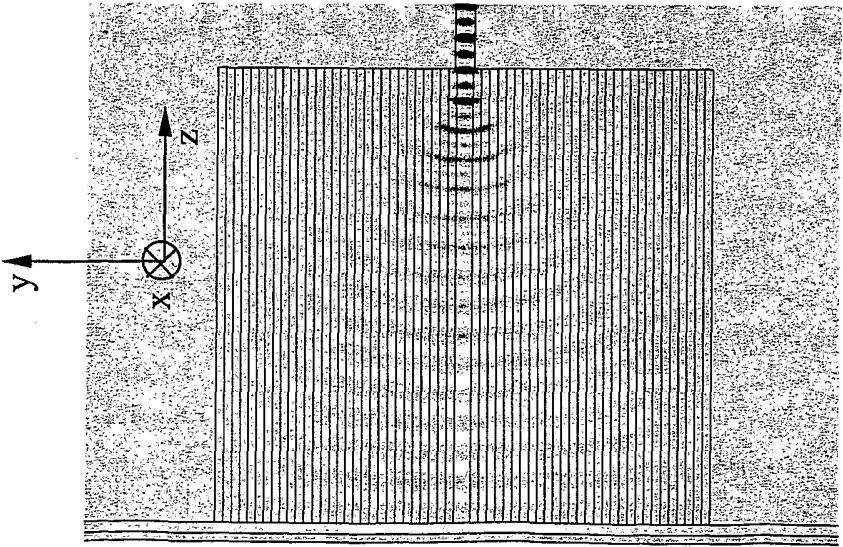


FIG. 7A

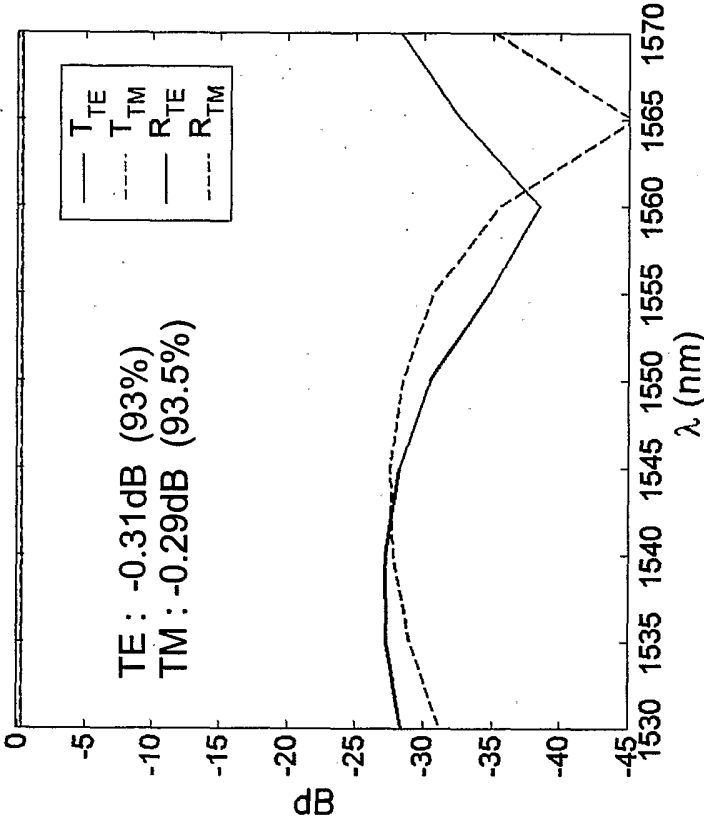


FIG. 7B

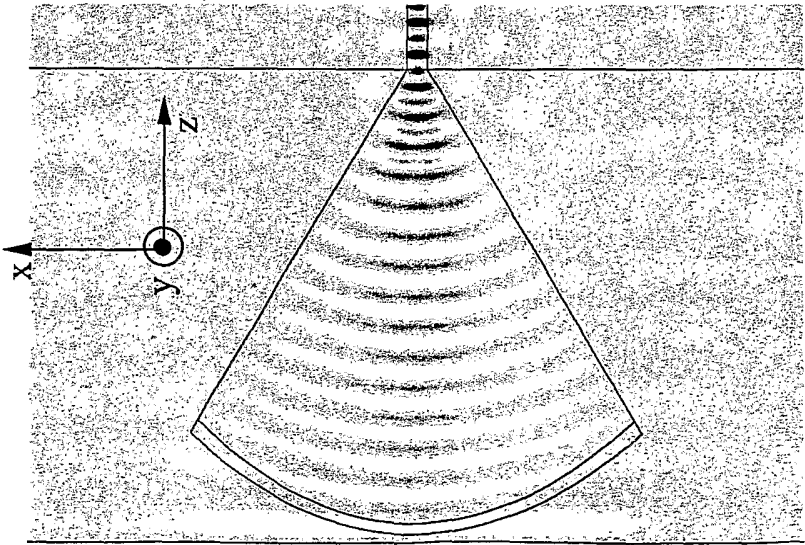


FIG. 7C

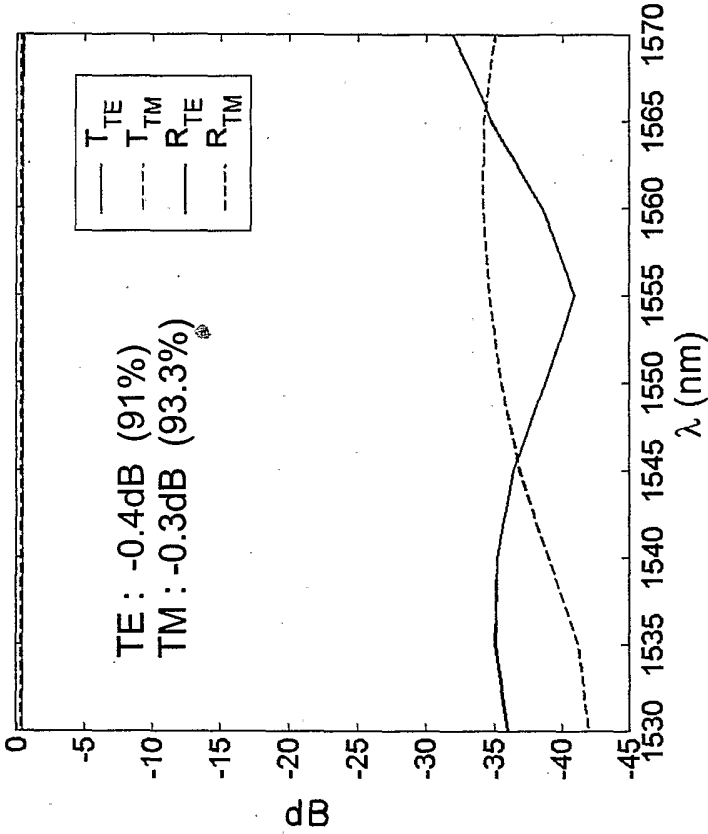
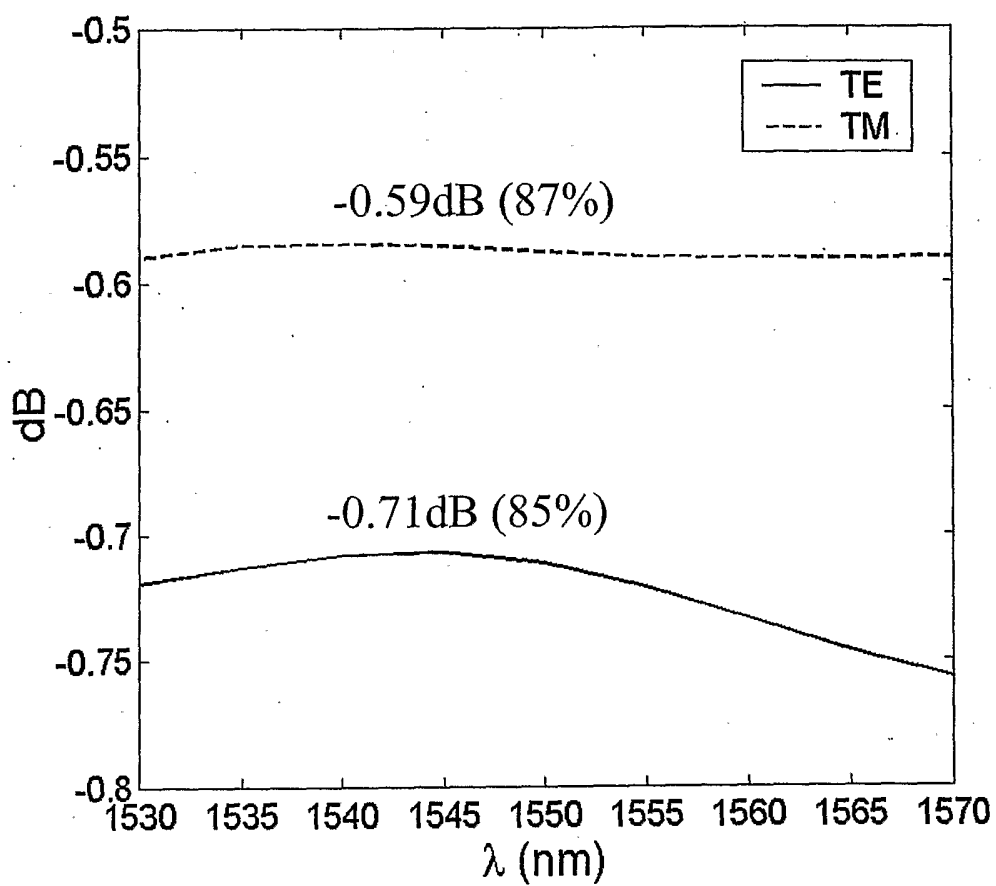


FIG. 7D

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***FIG. 7E***

INTERNATIONAL SEARCH REPORT

International Application No
PCT/US 02/24460

A. CLASSIFICATION OF SUBJECT MATTER
IPC 7 G02B6/12 G02B6/30

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
IPC 7 G02B

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the International search (name of data base and, where practical, search terms used)

EPO-Internal, WPI Data, PAJ

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category ^o	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	US 5 612 171 A (BHAGAVATULA VENKATA A) 18 March 1997 (1997-03-18) column 6, line 1 -column 7, line 18 figure 3	1
Y	----- PATENT ABSTRACTS OF JAPAN vol. 1998, no. 07, 31 March 1998 (1998-03-31) & JP 03 110504 A (FUJITSU LTD;BELL COMMUN RES INC), 10 May 1991 (1991-05-10) abstract ----- -/--	1



Further documents are listed in the continuation of box C.



Patent family members are listed in annex.

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Date of the actual completion of the international search

30 September 2002

Date of mailing of the international search report

07/10/2002

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Verdrager, V

INTERNATIONAL SEARCH REPORT

Int. Application No
PCT/US 02/24460

C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

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A	BHAGAVATULA V A ET AL: "PLANAR LENS DEVICES BY CVD PROCESS" PROCEEDINGS OF THE ELECTRONIC COMPONENTS AND TECHNOLOGY CONFERENCE. ORLANDO, JUNE 1 - 4, 1993, NEW YORK, IEEE, US, vol. CONF. 43, 1 June 1993 (1993-06-01), pages 988-991, XP000380101 ISSN: 0569-5503 paragraphs '0005!, '0007! figure 1	1
A	"INSTANTANEOUS AND CONTROLLED EXCITATION OF THE SPATIAL MODES IN PLANAR PROCESSED MULTI-MODE WAVEGUIDES OBTAINED BY LITHOGRAPHICALLY DEFINED LENSES IN THE WAVEGUIDE CORE" IBM TECHNICAL DISCLOSURE BULLETIN, IBM CORP. NEW YORK, US, vol. 36, no. 7, 1 July 1993 (1993-07-01), pages 423-426, XP000383685 ISSN: 0018-8689 figure 1	1
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A	US 6 160 927 A (LECLERC DENIS ET AL) 12 December 2000 (2000-12-12) figure 8	1,17,34
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INTERNATIONAL SEARCH REPORT

Inter ☐ National Application No
PCT/US 02/24460

C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	THURSTON R N ET AL: "TWO-DIMENSIONAL CONTROL OF MODE SIZE IN OPTICAL CHANNEL WAVEGUIDES BY LATERAL CHANNEL TAPERING" OPTICS LETTERS, OPTICAL SOCIETY OF AMERICA, WASHINGTON, US, vol. 16, no. 5, 1 March 1991 (1991-03-01), pages 306-308, XP000176116 ISSN: 0146-9592 abstract figure 3 -----	1,17,34

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